

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Yoshikazu KASUYA

Application No.: 10/689,990

Filed: October 22, 2003

Docket No.: 117588

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of reference No. 33 is discussed in the present specification.
- ☒ 3. The present application was filed or entered the U.S. National Stage of the PCT after June 30, 2003. In accordance with the June 11, 2003, Notice waiving the requirements of 37 C.F.R. §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- ☒ 4. English-language Abstracts of the non-English language references Nos. 30-32 are attached hereto.
- ☒ 5. A computer-generated English translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 30-32.

Respectfully submitted,



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DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
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Sheet 1 of 2

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117588		APPLICATION NO. 10/689,990	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT Yoshikazu KASUYA			
				FILING DATE October 22, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
	1	6,255,166 B1	07/03/2001	Ogura et al.			
	2	5,408,115	04/18/1995	Chang			
	3	5,969,383	10/19/1999	Chang et al.			
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	6	6,177,318 B1	01/23/2001	Ogura et al.			
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	8	US 2002-0100929	08/01/2002	Ebina et al.			
	9	US 2002-0127805	09/12/2002	Ebina et al.			
	10	6,413,821	07/02/2002	Ebina et al.			
	11	6,518,124	02/11/2003	Ebina et al.			
	12	US 2003-0054610	09/30/2003	Ebina et al.			
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	15	US 2003-0060011	03/27/2003	Ebina et al.			
	16	US 2003-0190805	10/09/2003	Inoue			
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	18	US 2003-0166321	09/04/2003	Kasuya			
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	24	10/636,581	08/08/2003	Yamamukai			
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	26	10/614,985	07/09/2003	Inoue			
	27	10/690,025	10/22/2003	Kasuya			
	28	10/689,987	10/22/2003	Kasuya			

Date: March 9, 2004



Sheet 2 of 2

29	10/689,993	10/22/2003	Kasuya		
FOREIGN PATENT DOCUMENTS					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
30	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan		
31	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan		
32	JP B1 2978477 (with abstract and translation)	09/10/1999	Japan		
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
33	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers				
34	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255				
35	Chen et al. "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers, pp 63-64				
EXAMINER			DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

Date: March 9, 2004